Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 10559-879001	Application No. 10/688,306
Information Disclosure Statement by Applicant (Use several sheets if necessary)		Applicant Yan Borodovsky	
(37 CFR §1.98(b))		Filing Date October 17, 2003	Group Art Unit 2851

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
	AE							
	AF							
	AG							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
RA	AH	M. Fritze, et al., "Gratings of regular arrays and trim exposures for ultralarge scale integrated circuit phase-shift lithography", *J. of Vacuum Science & Technology B*, 19(6):2366-2370, Nov/Dec 2001.
RA	AI	J.A. Hoffnagle, et al., "Liquid immersion deep-ultraviolet interferometric lithography" , *J. of Vacuum Science & Technology B*, 17(6):3306-3309, Nov/Dec 1999.
RA	AJ	Marc D. Levenson, et al., "Exposing the DUV SCAAM – 75 nm Imaging on the Cheap!", *Proc. of SPIE: Design, Process Integration, and Characterization for Microelectronics*, 4692:288-297, March 2002.
RA	AK	Alex K. Raub, et al., "Deep UV immersion interferometric lithography" , *Proc. of SPIE: Optical Microlithography XVI*, 5040:667-678, Feb. 2003.
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RA	AN	M. Switkes, et al., "Extending optics to 50 nm and beyond with immersion lithography" , *J. of Vacuum Science & Technology B*, 21(6):2794-2799, Nov/Dec 2003.
RA	AO	Brian Tyrrell, et al., "Investigation of the physical and practical limits of dense-only phase shift lithography for circuit feature definition" , *J. Microlith., Microfab., Microsyst.*, 1(3):244-252, Oct. 2002.
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RA	AQ	M. Fritze, et al., "Preprint of poster presentation entitled "High-Throughput Hybrid Optical Maskless Lithography: All-Optical 32-nm Node Imaging,", Presented at SPIE Microlithography 2005, San Jose, California, USA, March 3, 2005.

Examiner Signature	Date Considered
	8/3/05

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
RA	AA	2005/0073671	04/2005	Borodovsky			
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RA	AE	5,759,744	06/1998	Brueck, et al.			
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Foreign Patent Documents or Published Foreign Patent Applications

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	AL							
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	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

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RJ	AA	5,759,744	June 2, 1998	Brueck, et al.			
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RJ	AC	5,328,807	July 12, 1994	Tanaka, et al.			
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Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
RJ	AL	EP 0855623	July 29, 1998	EP				
RJ	AM	WO 98/32054	July 23, 1998	PCT				
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RJ	AQ	Ishibashi, et al., "AFM Lithography Combined with Optical Lithography", *IEEE Microprocesses and Nanotechnology Conference 2000*, pp. 192-193 (July 2000).
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RJ	8/3/05

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